

ABSTRACT

5       An object of the present invention is to provide a  
light-permeable electrode for use in a gallium nitride-  
based compound semiconductor light-emitting device, the  
electrode having improved light permeability and contact  
resistance.

10       The inventive electrode comprises a light-permeable  
first layer which is in contact with a surface of a p-  
contact layer in a gallium nitride-based compound  
semiconductor light-emitting device and which is capable  
of providing ohmic contact, and a second layer which is  
in contact with a part of a surface of said p-contact  
layer, wherein the first layer comprises a metal, or an  
15       alloy of two or more metals, selected from a first group  
consisting of Au, Pt, Pd, Ni, Co, and Rh, and the second  
layer comprises an oxide of at least one metal selected  
from a second group consisting of Ni, Ti, Sn, Cr, Co, Zn,  
Cu, Mg, and In.